

IN THE CLAIMS

1. (Currently Amended) ~~A method of making~~ The semiconductor structure of claim 20, prepared by a method comprising:

etching ~~an~~ the anti-reflective coating layer with an ARC etch plasma at a pressure of at most 10 millitorr;

etching a the nitride layer with a first nitride etch plasma having a first F:C ratio; and

etching the nitride layer with a second nitride etch plasma having a second F:C ratio;

wherein the first F:C ratio is greater than the second F:C ratio.

2-7. (Cancelled)

8. (Currently Amended) ~~The method of claim 5~~ semiconductor structure of claim 1, wherein the semiconductor structure comprises at most 8 drips per square centimeter.

9. (Currently Amended) ~~The method of claim 5~~ semiconductor structure of claim 1, wherein the semiconductor structure comprises at most 1 drip per square centimeter.

10-13. (Cancelled)

14. (Currently Amended) ~~A method of making a~~ The semiconductor structure of claim 20, prepared by a method comprising:

etching an anti-reflective coating layer at a pressure of at most 6 millitorr;

overetching the anti-reflective coating layer;

etching a nitride layer with a first nitride etch plasma having a F:C ratio of at least 3.8;

etching the nitride layer with a second nitride etch plasma having a F:C ratio at most 3.7; and

overetching the nitride layer with the second nitride etch plasma;

wherein the semiconductor structure has at most 1 drip per square centimeter, and has a minimum feature size of at most 1.8 micrometers.

15-19. (Cancelled)

20. (Original) A semiconductor structure, comprising:

a gate oxide;

a polysilicon layer on the gate oxide;

a silicon nitride layer on the polysilicon layer; and

an anti-reflective coating layer on the polysilicon layer;

wherein the semiconductor structure has a minimum feature size of at most 1.8 micrometers and has at most 10 drips per square centimeter.

21. (Original) The semiconductor structure of claim 20, having at most 8 drips per square centimeter.

22. (Original) The semiconductor structure of claim 20, having at most 1 drip per square centimeter.

23-25. (Cancelled)